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Wu et al.

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(54) **TFT ARRAY SUBSTRATE WITH STORAGE CAPACITOR HAVING LARGE CAPACITANCE AND LCD PANEL USING THE SAME**

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(51) **Int. Cl.**
G02F 1/1343 (2006.01)

(52) **U.S. Cl.** **385/39**

(58) **Field of Classification Search** 349/38,
349/143, 39

See application file for complete search history.

(56) **References Cited**

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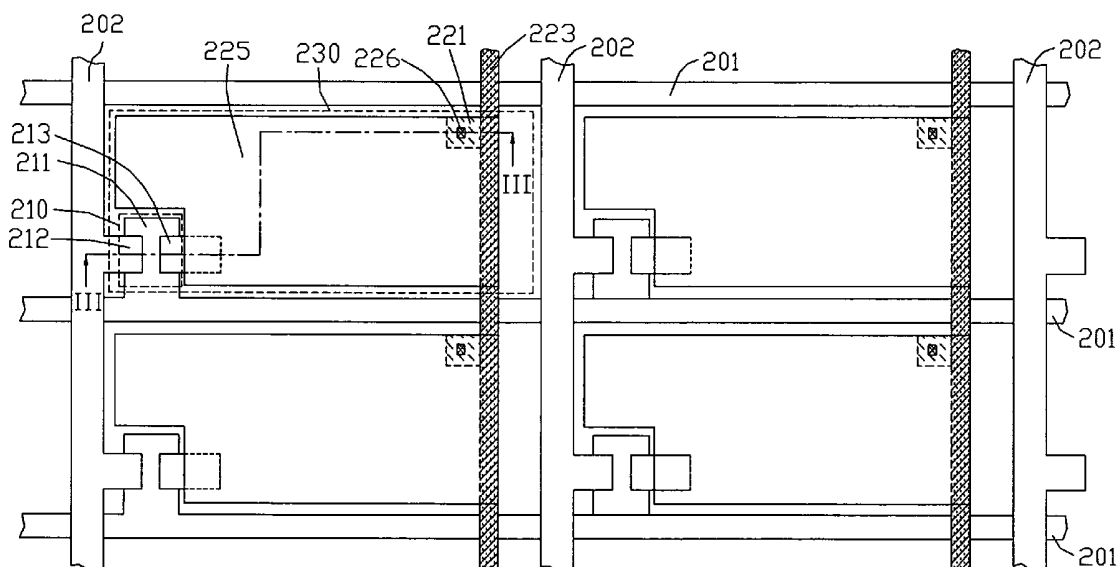
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(57) **ABSTRACT**

An exemplary thin film transistor array substrate (200) includes a transparent substrate (261), a plurality of gate lines (201) and a plurality of data lines (202) formed at the transparent substrate, the gate lines and the data lines crossing each other thereby defining a plurality of pixel regions (230). Each of the pixel regions includes a storage capacitor (220). The storage capacitor includes a first capacitor and a second capacitor aligned along a direction generally perpendicular to the transparent substrate, and the first capacitor and the second capacitor are electrically connected in parallel.

19 Claims, 4 Drawing Sheets



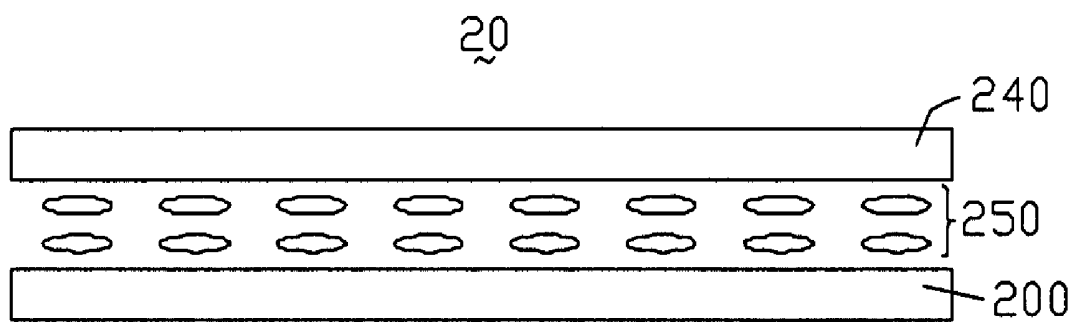


FIG. 1

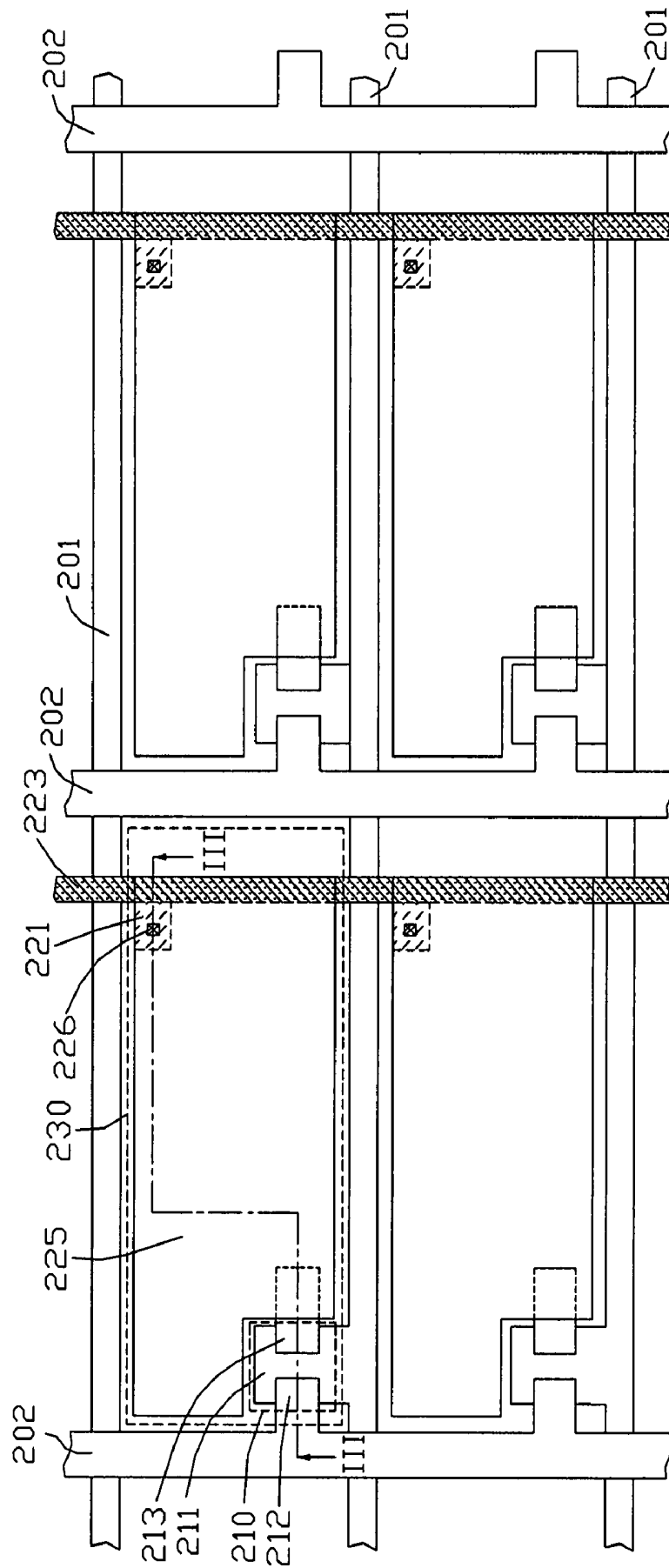


FIG. 2

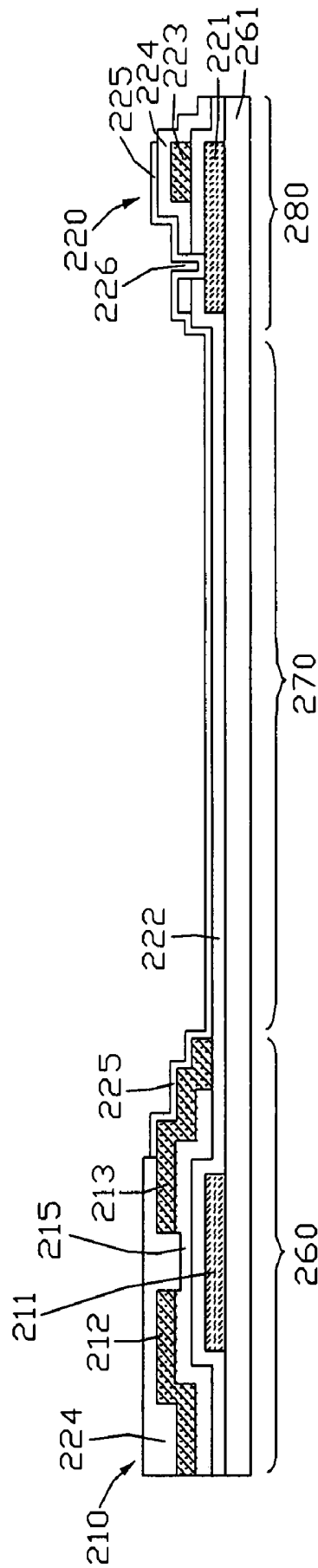


FIG. 3

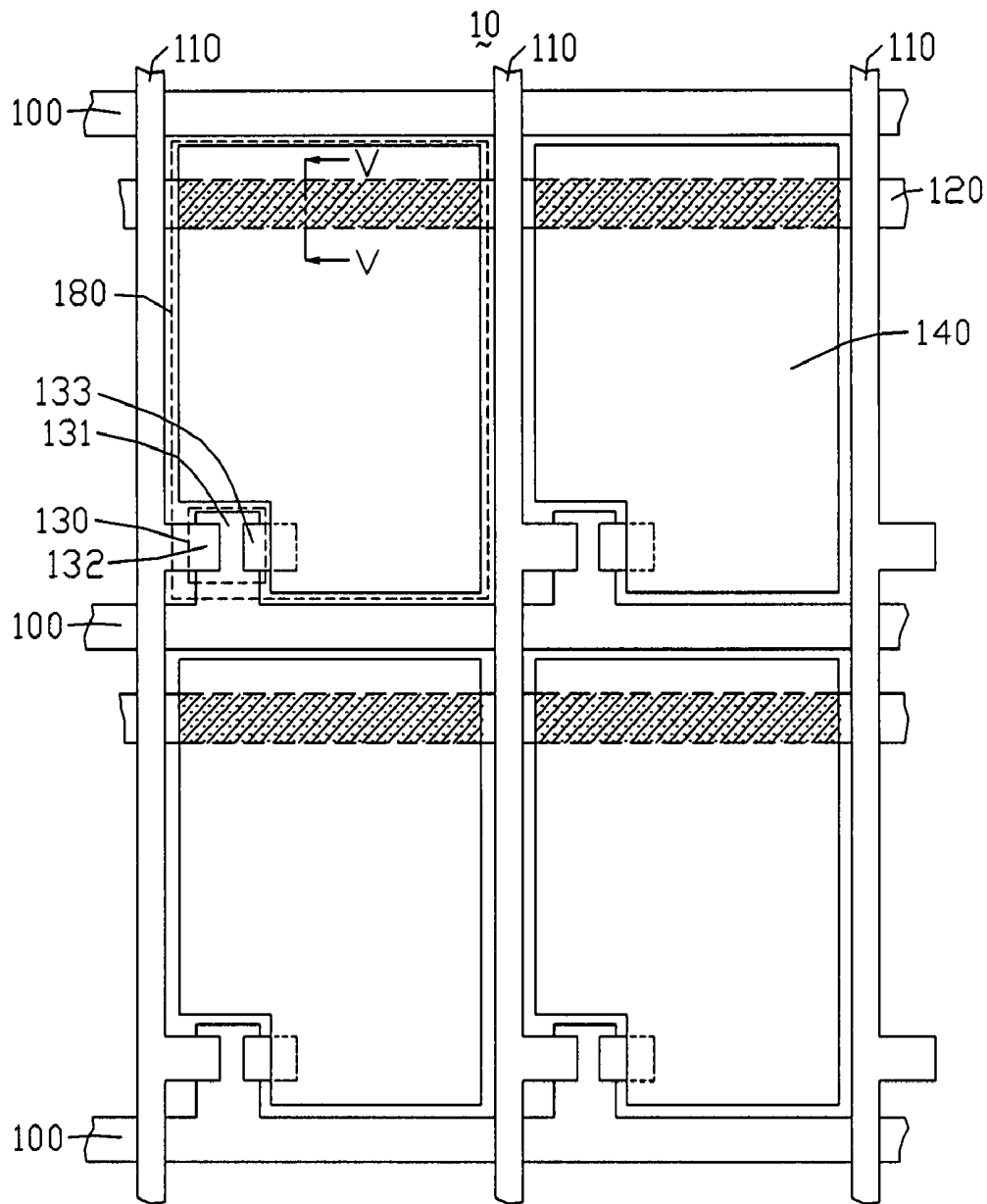


FIG. 4
(RELATED ART)

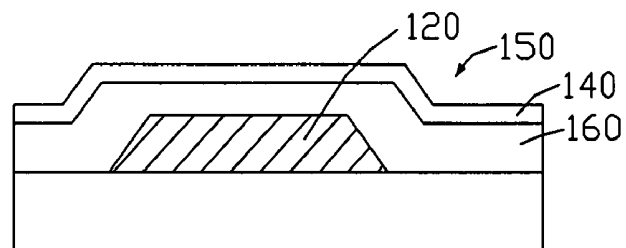


FIG. 5
(RELATED ART)

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TFT ARRAY SUBSTRATE WITH STORAGE CAPACITOR HAVING LARGE CAPACITANCE AND LCD PANEL USING THE SAME

FIELD OF THE INVENTION

The present invention relates to thin film transistor (TFT) array substrates and liquid crystal display (LCD) panels, and particularly to a TFT array substrate with storage capacitors having large capacitance and an LCD panel using the TFT array substrate.

BACKGROUND

A typical LCD is capable of displaying a clear and sharp image through thousands or even millions of pixels that make up the complete image. The LCD has thus been applied to various electronic equipments in which messages or pictures need to be displayed, such as mobile phones and notebook computers. An LCD panel is a major component of the LCD. The LCD panel generally includes a TFT array substrate, a color filter (CF) substrate opposite to the TFT array substrate, and a liquid crystal layer sandwiched between the two substrates.

FIG. 4 shows part of a typical TFT array substrate 10. FIG. 5 is an enlarged, cross-sectional view of part of the TFT array substrate 10, corresponding to line V-V of FIG. 4.

The TFT array substrate 10 includes a multiplicity of data lines 110 arranged parallel to each other and extending in a same direction, and a multiplicity of gate lines 100 arranged parallel to each other and extending in a direction perpendicular to the data lines 110. Thereby, the data lines 110 and gate lines 100 cooperatively define a multiplicity of pixel regions 180. Each of the pixel regions 180 includes a pixel electrode 140, a TFT 130 arranged at an intersection of a corresponding one of the data lines 110 and a corresponding one of the gate lines 100, a common electrode line 120 parallel to the gate line 100 and being partly overlapped by the pixel electrode 140, and an insulating layer 160 between the pixel electrode 140 and the common electrode line 120.

The TFT 130 includes a gate electrode 131 connected to the gate line 100 for receiving voltage control signals therefrom, a source electrode 132 connected to the data line 110 for receiving display signals therefrom, and a drain electrode 133 connected to the pixel electrode 140 for providing display signals thereto.

The overlapping portion of the pixel electrode 140, the insulating layer 160, and the common electrode line 120 cooperatively form a storage capacitor 150. It is important that the storage capacitor 150 have a larger capacitance for proper displaying of images. In order to display images better, there are two conventional ways for enlarging the capacitance of the storage capacitor 150: enlarging the area of the common electrode line 120, and reducing the thickness of the insulating layer 160. However, an enlarged area of the storage capacitor 150 decreases the aperture ratio of the LCD panel installed with the TFT array substrate 10. Further, the insulating layer 160 cannot be made very thin due to inherent limitations in manufacturing technology.

Accordingly, what is needed is a TFT array substrate for an LCD panel that can overcome the above-described deficiencies.

SUMMARY

In one preferred embodiment, a thin film transistor array substrate includes a transparent substrate, a plurality of gate

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lines and a plurality of data lines formed at the transparent substrate, the gate lines and the data lines crossing each other thereby defining a plurality of pixel regions. Each of the pixel regions includes a storage capacitor. The storage capacitor includes a first capacitor and a second capacitor aligned along a direction generally perpendicular to the transparent substrate, and the first capacitor and the second capacitor are electrically connected in parallel.

In an alternative embodiment, a liquid crystal display panel includes a color filter substrate and a thin film transistor array substrate opposite to each other, and a liquid crystal layer sandwiched between the color filter substrate and thin film transistor array substrates. The thin film transistor array substrate includes a transparent substrate, a plurality of gate lines and a plurality of data lines formed at the transparent substrate, the gate lines and the data lines crossing each other thereby defining a plurality of pixel regions. Each of the pixel regions includes a storage capacitor. The storage capacitor includes a first capacitor and a second capacitor aligned along a direction generally perpendicular to the transparent substrate, and the first capacitor and the second capacitor are electrically connected in parallel.

Other novel features and advantages will become more apparent from the following detailed description when taken in conjunction with the accompanying drawings. In the drawings, all the views are schematic.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 a side view of an LCD panel according to a preferred embodiment of the present invention.

FIG. 2 is an enlarged, top plan view of part of a TFT array substrate of the LCD panel of FIG. 1.

FIG. 3 is an enlarged, cross-sectional view of part of the TFT array substrate of FIG. 2, corresponding to line III-III thereof.

FIG. 4 is a top plan view of part of a TFT substrate of a conventional LCD panel.

FIG. 5 is an enlarged, cross-sectional view of part of the TFT array substrate of FIG. 4, corresponding to line V-V thereof.

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

FIG. 1 is a schematic, side view of an LCD panel according to a preferred embodiment of the present invention. The LCD panel 20 includes a thin film transistor (TFT) array substrate 200, a color filter (CF) substrate 240 disposed generally opposite to the TFT array substrate 200 with a predetermined distance therebetween, and a liquid crystal layer 250 interposed between the TFT array substrate 200 and the CF substrate 240.

Also referring to FIG. 2, this is an enlarged, top plan view of part of the TFT array substrate 200. A plurality of data lines 202 and gate lines 201 are formed on the TFT array substrate 200. The data lines 202 are arranged parallel to each other and extend along a longitudinal direction. The gate lines 201 are arranged parallel to each other and extend along a direction transverse to the data lines 202. Thus, the crossing data lines 202 and gate lines 201, cooperatively, define a multiplicity of pixel regions 230. Each of the pixel regions 230 has a rectangular shape having a long side and a short side, wherein the short side is parallel to the data lines 202.

Each pixel region 230 includes a thin film transistor (TFT) 210 arranged at an intersection of a corresponding one of the data lines 202 and a corresponding one of the gate lines 201,

a pixel electrode **225**, a common electrode line **223** parallel to the data lines **202**, a capacitor electrode **221** partly overlapped by the common electrode line **223**, and a contact hole **226** spanning between the pixel electrode **225** and the capacitor electrode **221**. All of the common electrode lines **223** can be connected together at corresponding same ends thereof, in order to receive common voltage signals for displaying images.

The TFT **210** includes a gate electrode **211** connected to the gate line **201** for receiving voltage control signals therefrom, a source electrode **212** connected to the data line **202** for receiving display signals therefrom, and a drain electrode **213** connected to the pixel electrode **225** for providing display signals thereto. When a voltage control signal is provided to the gate electrode **211** via the gate line **201** to turn on the TFT **210**, the display signals are provided to the pixel electrode **225** from the data line **202** via the source electrode **212** and drain electrode **213**.

Also referring to the FIG. 3, this is an enlarged, cross-sectional view of part of the TFT array substrate **200**, corresponding to line III-III of FIG. 2. Each of the pixel regions **230** includes three sub-regions: a TFT sub-region **260** corresponding to the TFT **210**, a storage capacitor sub-region **280** corresponding to a storage capacitor **220**, and a display sub-region **270** between the TFT sub-region **260** and the storage capacitor sub-region **280**.

The TFT array substrate **200** further includes a transparent substrate **261**, a first insulating layer **222**, a doped silicon layer **215**, and a second insulating layer **224**.

The gate electrode **211** and the capacitor electrode **221** are formed at a same layer on the transparent substrate **261**. The first insulating layer **222** is formed on the transparent substrate **261**, and covers the gate line **211**, the display sub-region **270**, and the capacitor electrode **221**. The doped silicon layer **215** is disposed on the first insulating layer **222** above and around the gate electrode **211**. The source electrode **212** and the drain electrode **213** are formed on two ends of the doped silicon layer **215**, and are symmetrically opposite each other. The common electrode line **223** is formed on the first insulating layer **222** above the capacitor electrode **221**. The source electrode **212**, the drain electrode **213**, and the common electrode line **223** can be formed at a same layer above the transparent substrate **261**. The second insulating layer **224** is formed on the source electrode **212**, the doped silicon layer **215**, and a portion of the drain electrode **213**, and on and around the common electrode line **223**. The pixel electrode **225** covers a portion of the drain electrode **213**, the first insulating layer **222** at the display sub-region **270**, and the part of the second insulating layer **224** covering the common electrode line **223**. The pixel electrode **225** is electrically connected to the capacitor electrode **221** via the contact hole **226**, which passes through the second insulating layer **224** and the first insulating layer **222**. In particular, the contact hole **226** contains a portion of the pixel electrode **225**, which electrically connects with the capacitor electrode **221**.

The capacitor electrode **221**, the first insulating layer **222**, and the common electrode line **223** cooperatively form a first capacitor. The common electrode line **223**, the second insulating layer **224**, and the pixel electrode **225** above the common electrode line **223** cooperatively form a second capacitor. The first capacitor and the second capacitor share the same common electrode line **223** as one of their capacitor electrodes. The pixel electrode **225** and the capacitor electrode **221** are electrically connected with each other via the contact hole **226**. Therefore the first and second capacitors are electrically connected in parallel, and cooperatively form a

single storage capacitor having a larger amount of capacitance to store a display voltage.

The above-described configuration provides an enlarged capacitance of the storage capacitor without expanding an area of the storage capacitor which overlies the transparent substrate **261**. This ensures that the LCD panel **20** can display images better, while keeping an aperture ratio of the LCD panel **20** as high as possible.

Moreover, in the above-described configuration, the common electrode line **223** is parallel to the short side of the pixel region **230**. Therefore the storage capacitor **220** formed by part of the common electrode line **223** occupies a relatively small area of the pixel region **230**. This configuration also helps ensure that the LCD panel **20** has a high aperture ratio.

Furthermore, all of the common electrode lines **223** of the LCD panel **20** can be connected together at corresponding same ends thereof, in order to receive common voltage signals for displaying images. This configuration makes it easier and more convenient to manufacture the LCD panel **20**.

It is to be further understood that even though numerous characteristics and advantages of various embodiments have been set forth in the foregoing description, together with details of the structures and functions of the embodiments, the disclosure is illustrative only, and changes may be made in detail to the full extent indicated by the broad general meaning of the terms in which the appended claims are expressed.

What is claimed is:

1. A thin film transistor array substrate, comprising:
a transparent substrate; and

a plurality of gate lines and a plurality of data lines formed at the transparent substrate, the gate lines and the data lines crossing each other thereby defining a plurality of pixel regions;

wherein each of the pixel regions comprises a storage capacitor, the storage capacitor comprises a first capacitor and a second capacitor aligned along a direction generally perpendicular to the transparent substrate, the first capacitor and the second capacitor are electrically connected in parallel, the first capacitor comprises a capacitor electrode, a common electrode line parallel to the capacitor electrode, and a first insulating layer sandwiched between the capacitor electrode and the common electrode line, and the second capacitor comprises the common electrode line, a pixel electrode parallel to the common electrode line, and a second insulating layer sandwiched between the common electrode line and the pixel electrode.

2. The thin film transistor array substrate as claimed in claim 1, wherein the pixel electrode is electrically connected to the capacitor electrode.

3. The thin film transistor array substrate as claimed in claim 2, wherein each of the pixel regions further comprises a contact hole passing through the first insulating layer and the second insulating layer, and the pixel electrode is electrically connected to the capacitor electrode via the contact hole.

4. The thin film transistor array substrate as claimed in claim 1, wherein each of the pixel regions has a rectangular shape with a long side and a short side, and the common electrode line is parallel to the short side.

5. The thin film transistor array substrate as claimed in claim 1, wherein each of the pixel regions further comprises a thin film transistor arranged at an intersection of a corresponding one of the gate lines and a corresponding one of the data lines.

6. The thin film transistor array substrate as claimed in claim 5, wherein the thin film transistor comprises a gate electrode electrically connected to the corresponding one of

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the gate lines, a source electrode electrically connected to the corresponding one of the data lines, and a drain electrode electrically connected to a corresponding storage capacitor.

7. The thin film transistor array substrate as claimed in claim 6, wherein the common electrode line is formed at a same layer with the data electrode and the gate electrode.

8. The thin film transistor array substrate as claimed in claim 6, wherein the capacitor electrode is formed at a same layer with the gate electrode.

9. A liquid crystal display panel, comprising:

a color filter substrate and a thin film transistor array substrate generally opposite to each other; and

a liquid crystal layer sandwiched between the color filter substrate and the thin film transistor array substrate;

wherein the thin film transistor array substrate comprises: a transparent substrate; and

a plurality of gate lines and a plurality of data lines formed at the transparent substrate, the gate lines and the data lines crossing each other thereby defining a plurality of pixel regions;

each of the pixel regions comprising a storage capacitor, the storage capacitor comprising a first capacitor and a second capacitor aligned along a direction generally perpendicular to the transparent substrate, and the first capacitor and the second capacitor being electrically connected in parallel, wherein the first capacitor comprises a capacitor electrode, a common electrode line parallel to the capacitor electrode, and a first insulating layer sandwiched between the capacitor electrode and the common electrode line, and the second capacitor comprises the common electrode line, a pixel electrode parallel to the common electrode line, and a second insulating layer sandwiched between the common electrode line and the pixel electrode.

10. The liquid crystal display panel as claimed in claim 9, wherein each of the pixel regions further comprises a thin film transistor arranged at an intersection of a corresponding one of the gate lines and a corresponding one of the data lines.

11. The liquid crystal display panel as claimed in claim 10, wherein the thin film transistor comprises a gate electrode electrically connected to the corresponding one of the gate lines, a source electrode electrically connected to the corresponding one of the data lines, and a drain electrode electrically connected to a corresponding storage capacitor.

12. The liquid crystal display panel as claimed in claim 9, wherein the pixel electrode is electrically connected to the capacitor electrode.

13. The liquid crystal display panel as claimed in claim 12, wherein each of the pixel regions further comprises a contact

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hole passing through the first insulating layer and the second insulating layer, and the pixel electrode is electrically connected to the capacitor electrode via the contact hole.

14. The liquid crystal display panel as claimed in claim 9, wherein each of the pixel regions has a rectangular shape with a long side and a short side, and the common electrode line is parallel to the short side.

15. A thin film transistor array substrate, comprising: a transparent substrate; and

a plurality of gate lines and a plurality of data lines formed at the transparent substrate, the gate lines and the data lines crossing each other thereby defining a plurality of pixel regions, each of the pixel regions having a rectangular shape with a long side and a short side;

wherein each of the pixel regions comprises a storage capacitor, the storage capacitor comprises a first capacitor and a second capacitor aligned along a direction generally perpendicular to the transparent substrate, and the first capacitor and the second capacitor are electrically connected in parallel; and

wherein the second capacitor comprises a common electrode line, a pixel electrode facing toward the common electrode line, and an insulating layer sandwiched between the common electrode line and the pixel electrode, and the common electrode line is parallel to the short side.

16. The thin film transistor array substrate as claimed in claim 15, wherein each of the pixel regions further comprises a thin film transistor arranged at an intersection of a corresponding one of the gate lines and a corresponding one of the data lines, and each thin film transistor comprises a gate electrode electrically connected to the corresponding one of the gate lines, a source electrode electrically connected to the corresponding one of the data lines, and a drain electrode electrically connected to a corresponding storage capacitor.

17. The thin film transistor array substrate as claimed in claim 16, wherein the common electrode line is formed at a same layer with the data electrode and the gate electrode.

18. The thin film transistor array substrate as claimed in claim 16, wherein in each pixel region, the first capacitor and the second capacitor share a same common electrode line.

19. The thin film transistor array substrate as claimed in claim 18, wherein the first capacitor comprises a capacitor electrode facing towards the common electrode line, and the capacitor electrode is formed at a same layer with the gate electrode.

* * * * *

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,885,497 B2
APPLICATION NO. : 11/811508
DATED : February 8, 2011
INVENTOR(S) : Tian-Yi Wu and Kai Meng

Page 1 of 1

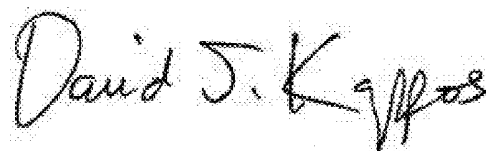
It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page;

Please replace Section (73) regarding “Assignees” on the front page of the Patent with the following:

(73) Assignees: Innocom Technology (Shenzhen) Co., Ltd., Shenzhen,
Guangdong Province (CN); Chimei Innolux Corporation,
Miao-Li County (TW).

Signed and Sealed this
Seventh Day of June, 2011

A handwritten signature in black ink, reading "David J. Kappos". The signature is written in a cursive, flowing style with a large initial 'D' and 'K'.

David J. Kappos
Director of the United States Patent and Trademark Office

专利名称(译)	具有大电容的存储电容器的TFT阵列基板和使用其的LCD面板		
公开(公告)号	US7885497	公开(公告)日	2011-02-08
申请号	US11/811508	申请日	2007-06-11
[标]申请(专利权)人(译)	群创光电股份有限公司		
申请(专利权)人(译)	群创光电股份有限公司.		
当前申请(专利权)人(译)	奇美群创光电 INNOCOM科技(深圳)有限公司.		
[标]发明人	WU TIAN YI MENG KAI		
发明人	WU, TIAN-YI MENG, KAI		
IPC分类号	G02F1/1343		
CPC分类号	G02F1/136213		
优先权	200610061064.8 2006-06-09 CN		
其他公开文献	US20070285590A1		
外部链接	Espacenet USPTO		

摘要(译)

示例性薄膜晶体管阵列基板(200)包括透明基板(261), 多条栅极线(201)和形成在透明基板上的多条数据线(202), 栅极线和数据线交叉其他由此限定多个像素区域(230)。每个像素区域包括存储电容器(220)。存储电容器包括沿大致垂直于透明基板的方向排列的第一电容器和第二电容器, 并且第一电容器和第二电容器并联电连接。

